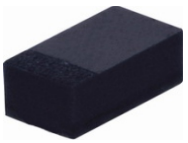
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

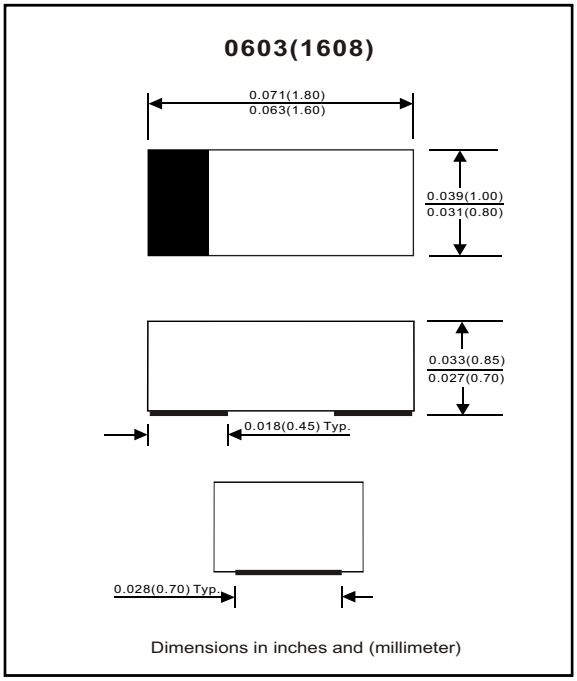
CDBUR0230(RoHs Device)

Io = 200 mA
V_R = 30 Volts



Features

- Designed for mounting on small surface.
- Extremely thin/leadless package.
- Low drop-down voltage.
- Majority carrier conduction.



Mechanical data

Case: 0603(1608) standard package, molded plastic.

Terminals: Gold plated, solderable per MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).

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Maximum Rating (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		V_{RRM}			35	V
Reverse voltage		V_R			30	V
Average forward current		I_O			200	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	I_{FSM}		3000		mA
Power Dissipation		P_D			150	mW
Sunction temperature		T_{STG}	-40		+125	°C
Junction temperature		T_j			+125	°C

Electrical Characteristics (at T_A=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F = 200 mA DC	V_F			0.50	V
Reverse current	V_R = 30V	I_R			30	uA
Capacitance between terimnals	F = 1 MHZ and 10 VDC reverse voltage	C_T		9		pF

RATING AND CHARACTERISTIC CURVES (CDBUR0230)

Fig. 1 - Forward characteristics

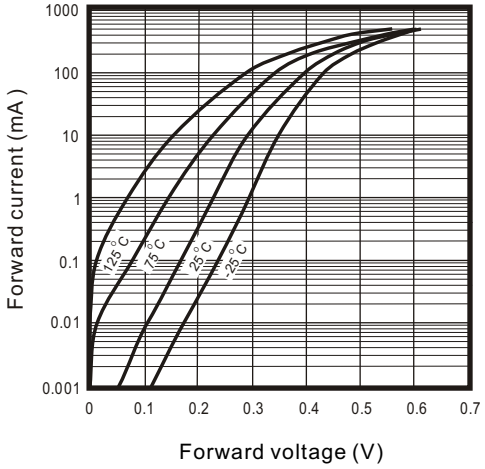

Fig. 2 - Reverse characteristics

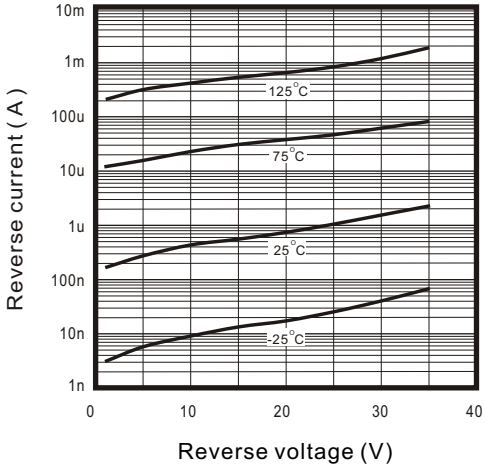

Fig.3 - Capacitance between terminals characteristics

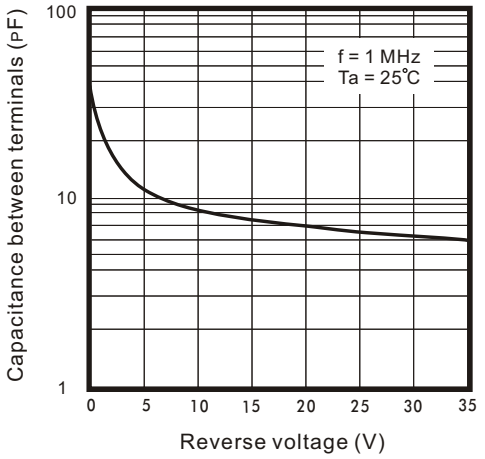

Fig.4 - Current derating curve